

Title (en)

LOW OXIDE TRENCH DISHING SHALLOW TRENCH ISOLATION CHEMICAL MECHANICAL PLANARIZATION POLISHING

Title (de)

CHEMISCH-MECHANISCHE PLANARISIERUNGSPOLIERZUSAMMENSETZUNGEN MIT OXIDARMER GRABENBOMBIERUNG FÜR ANWENDUNGEN ZUR ISOLIERUNG VON FLACHEN GRÄBEN

Title (fr)

PLANARISATION PAR POLISSAGE CHIMICO-MÉCANIQUE D'ISOLATION PAR TRANCHÉES PEU PROFONDES À FAIBLE BOMBAGE DE TRANCHÉES D'OXYDE

Publication

**EP 4073187 A1 20221019 (EN)**

Application

**EP 20898454 A 20201021**

Priority

- US 201916711818 A 20191212
- TW 109135359 A 20201013
- US 2020056673 W 20201021

Abstract (en)

[origin: WO2021118694A1] The present invention discloses STI CMP polishing compositions, methods and systems that significantly reduce oxide trench dishing and improve over-polishing window stability in addition to provide high and tunable silicon oxide removal rates, low silicon nitride removal rates, and tunable high selectivity of SiO<sub>2</sub>: SiN through the use of an unique combination of ceria inorganic oxide particles, such as ceria coated silica particles as abrasives, and an oxide trench dishing reducing additive of poly(methacrylic acids), its derivatives, its salts, or combinations thereof.

IPC 8 full level

**C09G 1/02** (2006.01); **C09K 3/14** (2006.01); **H01L 21/02** (2006.01); **H01L 21/3105** (2006.01); **H01L 21/762** (2006.01)

CPC (source: EP IL KR)

**C09G 1/02** (2013.01 - EP IL KR); **C09K 3/1445** (2013.01 - EP IL KR); **H01L 21/31053** (2013.01 - EP IL KR); **H01L 21/76224** (2013.01 - IL); **C09K 3/1463** (2013.01 - EP); **H01L 21/76224** (2013.01 - EP KR)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

**WO 2021118694 A1 20210617**; EP 4073187 A1 20221019; EP 4073187 A4 20231213; IL 293769 A 20220801; JP 2023506487 A 20230216; KR 20220113497 A 20220812

DOCDB simple family (application)

**US 2020056673 W 20201021**; EP 20898454 A 20201021; IL 29376922 A 20220609; JP 2022535706 A 20201021; KR 20227023858 A 20201021